

1 58 and 60 are reproduced below without change in order that all of the  
2 claims being prosecuted may be easily viewed together.

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4 44. (Fourfold Amended) A pair of adjacent stacked capacitors  
5 fabricated using a photolithographic process having a characteristic  
6 minimum photolithographic feature dimension on [relative to] a  
7 semiconductor substrate, the adjacent stacked capacitors respectively  
8 including a lower plate having a minimum lateral spacing from one  
9 another which is less than [a] the minimum photolithographic feature  
10 dimension [with which the capacitors are fabricated], each lower plate  
11 including a polysilicon plug having a diameter less than the minimum  
12 photolithographic feature dimension.

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1           45. (Thrice Amended) [The capacitors of claim 44] A pair of  
2           adjacent stacked capacitors fabricated using a photolithographic process  
3           having a characteristic minimum photolithographic feature dimension on  
4           a semiconductor substrate, the adjacent stacked capacitors respectively  
5           including a lower plate having a minimum lateral spacing from one  
6           another which is less than the minimum photolithographic feature  
7           dimension wherein each of the pair of capacitors comprises:

8            a [stem] polysilicon plug having a diameter less than the minimum  
9           photolithographic feature dimension; and

10           *Cont'd*  
11           in cross-section, at least two laterally opposed fins interconnected  
12           with and projecting laterally from the [stem] plug[, the stem having a  
13           minimum width which is less than the minimum photolithographic feature  
14           dimension].

15           51. The capacitors of claim 44, wherein the lower plates are  
16           formed from conductive polysilicon.

17           52. (Amended) The capacitors of claim 45, wherein the [stem]  
18           plug and fins are formed from conductive polysilicon.

21           53. The capacitors of claim 45, wherein the pair of stacked  
22           capacitors are coated with a capacitor dielectric layer.

1           54. (Amended) A pair of adjacent stacked capacitors fabricated  
2        using a photolithographic process having a characteristic minimum  
3        photolithographic feature dimension on [relative to] a semiconductor  
4        substrate, the adjacent stacked capacitors respectively including a lower  
5        plate having a minimum lateral spacing from one another which is less  
6        than [a] the minimum photolithographic feature dimension, each lower  
7        plate comprising a [stem] polysilicon plug having a diameter that is less  
8        than the minimum photolithographic feature dimension and, in cross-  
9        section, at least two laterally opposed fins interconnected with and  
10      projecting laterally from the plug [stem].

*Cont'd*

*E*

11            Cancel claim 55.

*P*  
*cont*

12           56. (Amended) The capacitors of claim 54 wherein the [stem]  
13        plug includes a minimum width which is less than the minimum  
14        photolithographic feature dimension.

15            Cancel claim 57.

16           58. The capacitors of claim 54, wherein the lower plates are  
17        formed from conductive polysilicon.

1           59. (Amended) The capacitors of claim 54, wherein the [stem]  
2       plug and fins are formed from conductive polysilicon.

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4           60. The capacitors of claim 54, wherein the pair of stacked  
5       capacitors are coated with a capacitor dielectric layer.  
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7           Cont'd  
8           Cancel claim 61.]

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10          62. (Amended) [The capacitors of claim 61] A pair of adjacent  
11       stacked capacitors fabricated using a photolithographic process having a  
12       characteristic minimum photolithographic feature dimension on a  
13       semiconductor substrate, the adjacent stacked capacitors respectively  
14       including a finned lower plate having a minimum lateral spacing from  
15       one another which is less than the minimum photolithographic feature  
16       dimension wherein each finned lower plate comprises:

17           a [stem] polysilicon plug; and

18           in cross-section, at least two laterally opposed fins interconnected  
19       with and projecting laterally from the [stem] plug, the [stem] plug having  
20       a minimum width which is less than the minimum photolithographic  
21       feature dimension.

22           Cancel claims 63-65.]

1           66. (Amended) The capacitors of claim [61] 62, wherein the  
2 lower plates are formed from conductive polysilicon.

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4           67. (Amended) The capacitors of claim 62, wherein the [stem]  
5 plug and fins are formed from conductive polysilicon.  
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8           68. (Amended) The capacitors of claim [61] 62, wherein the pair  
9 of stacked capacitors are coated with a capacitor dielectric layer.

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